Preliminary datasheet

EconoPIM™2 module with TRENCHSTOP™IGBT7 and emitter controlled 7 diode and Vienna rectifier PFC

Features

Typical appearance

- Electrical features
  - V_{CES} = 1200 V
  - $I_{C\ nom}$ = 35 A / I_{CRM} = 70 A
  - TRENCHSTOP™ IGBT7
  - Trench IGBT 5
  - $T_{vj,op}$ = 150°C
  - Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder
- Mechanical features
  - High power and thermal cycling capability
  - Integrated NTC temperature sensor
  - Standard housing
  - Copper base plate
  - Al_2O_3 substrate with low thermal resistance
  - Solder contact technology

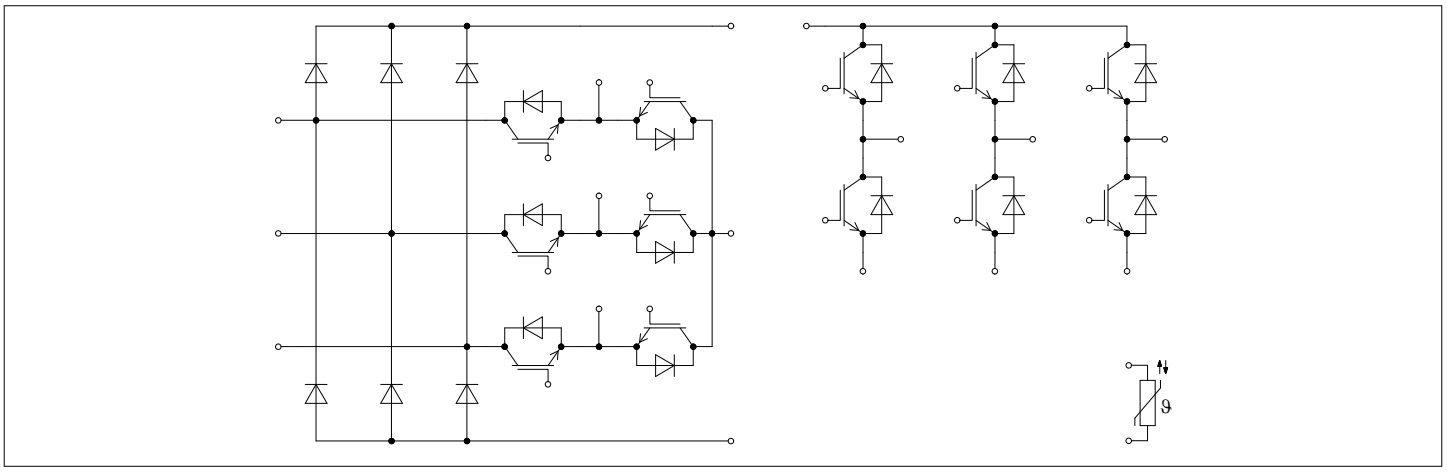
Potential applications

- Residential HVAC

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	2.5	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, f = 50 Hz, *t* = 1 min	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	$d_{Creep\ nom}$	terminal to baseplate, nom., (PD2, IEC 60664-1, Ed. 3.0)	10.0	mm
Clearance	$d_{Clear\ nom}$	terminal to baseplate, nom.	7.5	mm
Comparative tracking index	*CTI*		> 200	
Relative thermal index (electrical)	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				36		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_C = 25 °C, per switch			8.4		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C = 25 °C, per switch			4.4		mΩ
Storage temperature	T_{stg}			-40		125	°C
Mounting torque for module mounting	*M*	- Mounting according to valid application note	M5, Screw	3		6	Nm
Weight	*G*				180		g

***Note**: The current under continuous operation is limited to 50A rms per connector pin.*

2 IGBT, T1-T6

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj\ max}$ = 175 °C	T_C = 115 °C	35	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$		70	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 35 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.60	1.85	V
			T_{vj} = 125 °C		1.74		
			T_{vj} = 150 °C		1.78		
Gate threshold voltage	V_{GEth}	I_C = 0.75 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.8	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 600 V, T_{vj} = 25 °C			0.55		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0.0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			6.62		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.023		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.004	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 35 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Gon} = 3 Ω	T_{vj} = 25 °C		0.021		µs
			T_{vj} = 125 °C		0.025		
			T_{vj} = 150 °C		0.025		
Rise time (inductive load)	t_r	I_C = 35 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Gon} = 3 Ω	T_{vj} = 25 °C		0.016		µs
			T_{vj} = 125 °C		0.018		
			T_{vj} = 150 °C		0.019		
Turn-off delay time (inductive load)	t_{doff}	I_C = 35 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Goff} = 2 Ω	T_{vj} = 25 °C		0.207		µs
			T_{vj} = 125 °C		0.283		
			T_{vj} = 150 °C		0.300		
Fall time (inductive load)	t_f	I_C = 35 A, V_{CC} = 600 V, V_{GE} = ±15 V, R_{Goff} = 2 Ω	T_{vj} = 25 °C		0.121		µs
			T_{vj} = 125 °C		0.218		
			T_{vj} = 150 °C		0.249		
Turn-on energy loss per pulse	E_{on}	I_C = 35 A, V_{CC} = 600 V, L_σ = 36 nH, V_{GE} = ±15 V, R_{Gon} = 3 Ω, di/dt = 1720 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		1.71		mJ
			T_{vj} = 125 °C		2.82		
			T_{vj} = 150 °C		3.15		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	I_C = 35 A, V_{CC} = 600 V, L_σ = 36 nH, V_{GE} = ±15 V, R_{Goff} = 2 Ω, dv/dt = 3420 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		2.08		mJ
			T_{vj} = 125 °C		3.44		
			T_{vj} = 150 °C		3.84		
SC data	I_{SC}	V_{GE} ≤ 15 V, V_{CC} = 800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P ≤ 6 µs, T_{vj} = 125 °C		120		A
			t_P ≤ 8 µs, T_{vj} = 150 °C		115		
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.802	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT			0.157		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

3 Diode, D1-D6

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continuous DC forward current	I_F			35	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		70	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	205	A^2s
			T_{vj} = 150 °C	190	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 35 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.72	2.10	V
			T_{vj} = 125 °C		1.59		
			T_{vj} = 150 °C		1.55		
Peak reverse recovery current	I_{RM}	V_{CC} = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 1720 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		39.4		A
			T_{vj} = 125 °C		45.7		
			T_{vj} = 150 °C		47		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	V_{CC} = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 1720 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3		µC
			T_{vj} = 125 °C		5.4		
			T_{vj} = 150 °C		6.2		
Reverse recovery energy	E_{rec}	V_{CC} = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 1720 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		1.17		mJ
			T_{vj} = 125 °C		2.08		
			T_{vj} = 150 °C		2.4		
Thermal resistance, junction to case	R_{thJC}	per diode				1.10	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode			0.176		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

4 IGBT, T7-T12

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Implemented collector current	I_{CN}			35	A
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 150 °C	T_C = 115 °C	20	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		70	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 35 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.60	2.20	V
			T_{vj} = 125 °C		1.74		
			T_{vj} = 150 °C		1.78		
Gate threshold voltage	V_{GEth}	I_C = 0.35 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		3.85	4.6	5.35	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 300 V, T_{vj} = 25 °C			0.152		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0.0		Ω

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			1.94		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.007		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.013	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 35 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 1.8 Ω	T_{vj} = 25 °C		0.012		µs
			T_{vj} = 125 °C		0.012		
			T_{vj} = 150 °C		0.013		
Rise time (inductive load)	t_r	I_C = 35 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Gon} = 1.8 Ω	T_{vj} = 25 °C		0.008		µs
			T_{vj} = 125 °C		0.010		
			T_{vj} = 150 °C		0.011		
Turn-off delay time (inductive load)	t_{doff}	I_C = 35 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 2.4 Ω	T_{vj} = 25 °C		0.065		µs
			T_{vj} = 125 °C		0.081		
			T_{vj} = 150 °C		0.084		
Fall time (inductive load)	t_f	I_C = 35 A, V_{CC} = 300 V, V_{GE} = ±15 V, R_{Goff} = 2.4 Ω	T_{vj} = 25 °C		0.010		µs
			T_{vj} = 125 °C		0.019		
			T_{vj} = 150 °C		0.021		
Turn-on energy loss per pulse	E_{on}	I_C = 35 A, V_{CC} = 300 V, L_σ = 36 nH, V_{GE} = ±15 V, R_{Gon} = 1.8 Ω, di/dt = 2600 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.216		mJ
			T_{vj} = 125 °C		0.301		
			T_{vj} = 150 °C		0.323		
Turn-off energy loss per pulse	E_{off}	I_C = 35 A, V_{CC} = 300 V, L_σ = 36 nH, V_{GE} = ±15 V, R_{Goff} = 2.4 Ω, dv/dt = 9910 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.14		mJ
			T_{vj} = 125 °C		0.29		
			T_{vj} = 150 °C		0.33		
Thermal resistance, junction to case	R_{thJC}	per IGBT				1.20	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT			0.178		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

5 Diode, D7-D12

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Continuous DC forward current	I_F			30	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		60	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	100	A^2s
			T_{vj} = 150 °C	80	

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 30 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.60	2.00	V
			T_{vj} = 125 °C		1.55		
			T_{vj} = 150 °C		1.52		
Thermal resistance, junction to case	R_{thJC}	per diode				1.44	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode			0.182		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

6 Diode, D13-D18

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Implemented forward current	I_{FN}			50	A
Continuous DC forward current	I_F			35	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		100	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	295	A^2s
			T_{vj} = 150 °C	290	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 35 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.72	2.10	V
			T_{vj} = 125 °C		1.59		
			T_{vj} = 150 °C		1.55		
Peak reverse recovery current	I_{RM}	V_{CC} = 300 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 2580 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		68.8		A
			T_{vj} = 125 °C		81.8		
			T_{vj} = 150 °C		87.6		
Recovered charge	Q_r	V_{CC} = 300 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 2580 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		2.9		µC
			T_{vj} = 125 °C		5.7		
			T_{vj} = 150 °C		6.7		
Reverse recovery energy	E_{rec}	V_{CC} = 300 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 2580 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.77		mJ
			T_{vj} = 125 °C		1.5		
			T_{vj} = 150 °C		1.76		
Thermal resistance, junction to case	R_{thJC}	per diode				0.900	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode			0.168		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

7 NTC-Thermistor

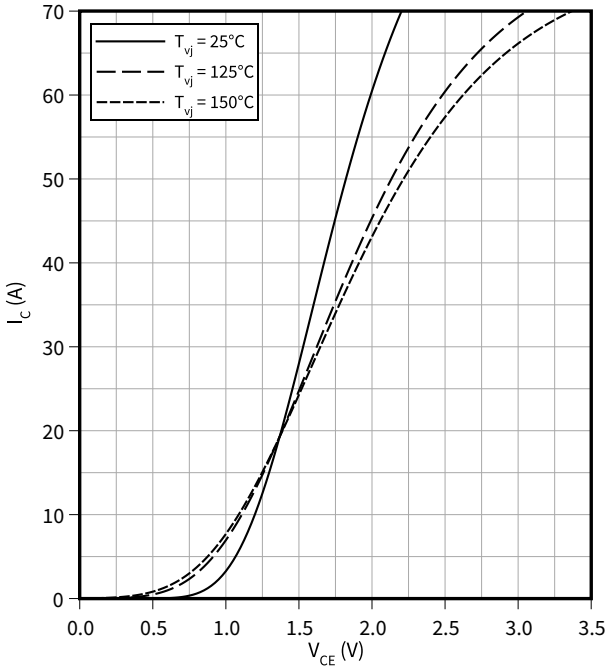
Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

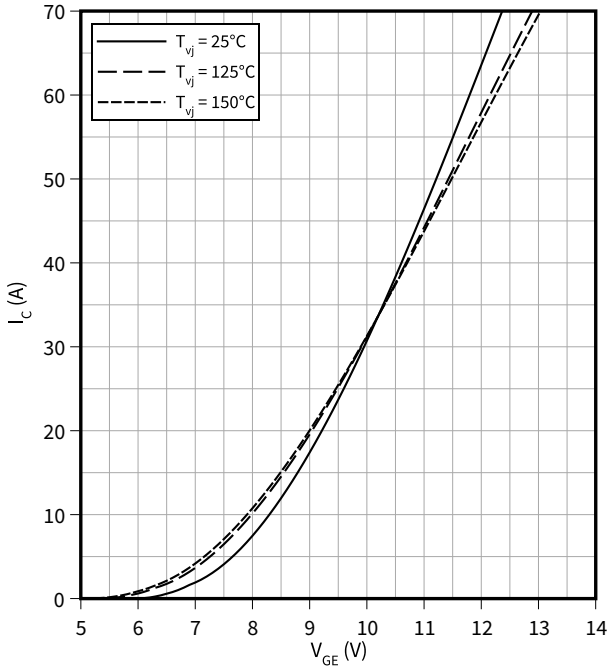
***Note**: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4.*

8 Characteristics diagrams

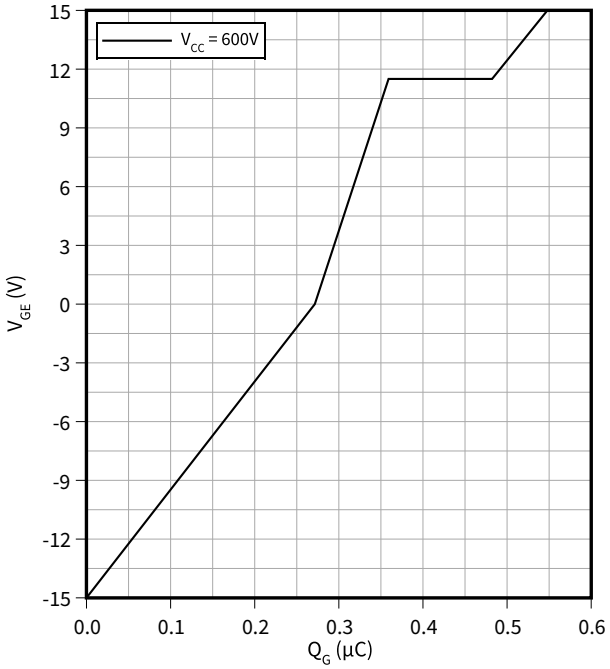
Output characteristic (typical), IGBT, T1-T6
$I_C = f(V_{CE})$
V_{GE} = 15 V



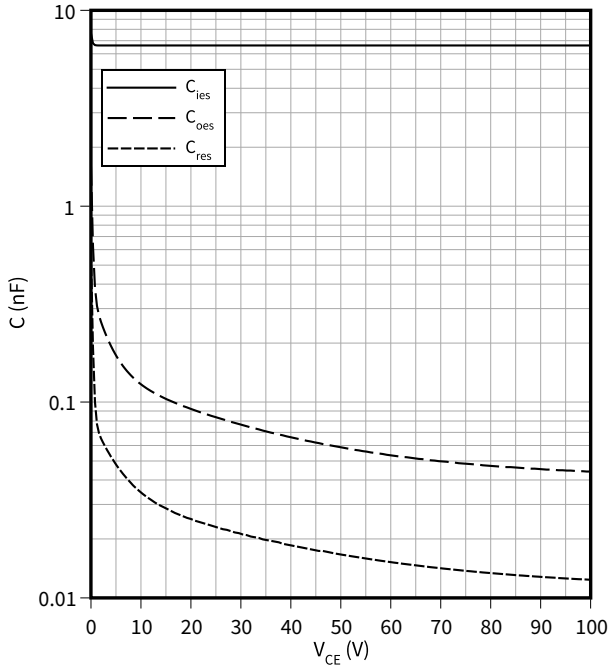
Transfer characteristic (typical), IGBT, T1-T6
$I_C = f(V_{GE})$
V_{CE} = 20 V



Gate charge characteristic (typical), IGBT, T1-T6
$V_{GE} = f(Q_G)$
I_C = 35 A, T_{vj} = 25 °C



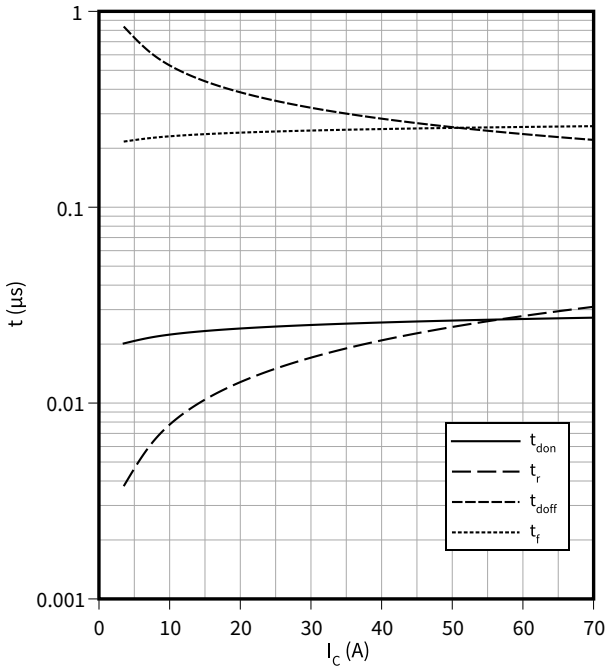
Capacity characteristic (typical), IGBT, T1-T6
$C = f(V_{CE})$
f = 100 kHz, V_{GE} = 0 V, T_{vj} = 25 °C



Switching times (typical), IGBT, T1-T6

$t = f(I_C)$

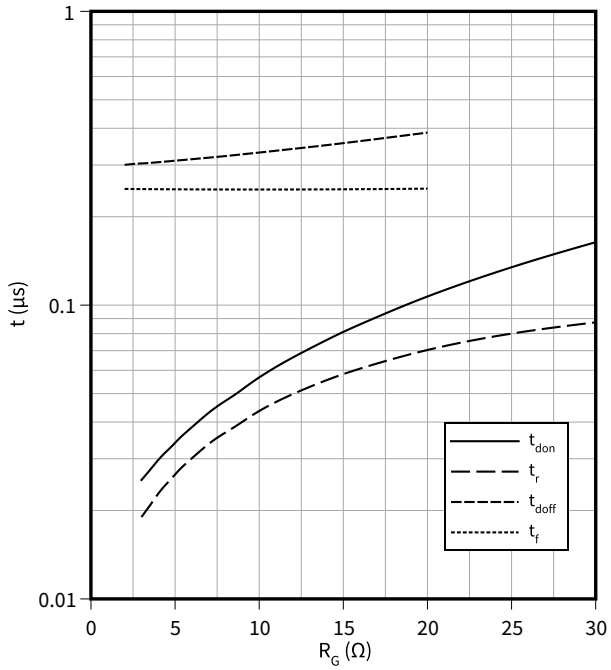
R_{Goff} = 2 Ω, R_{Gon} = 3 Ω, V_{CC} = 600 V, -15 / 15 V, T_{vj} = 150 °C



Switching times (typical), IGBT, T1-T6

$t = f(R_G)$

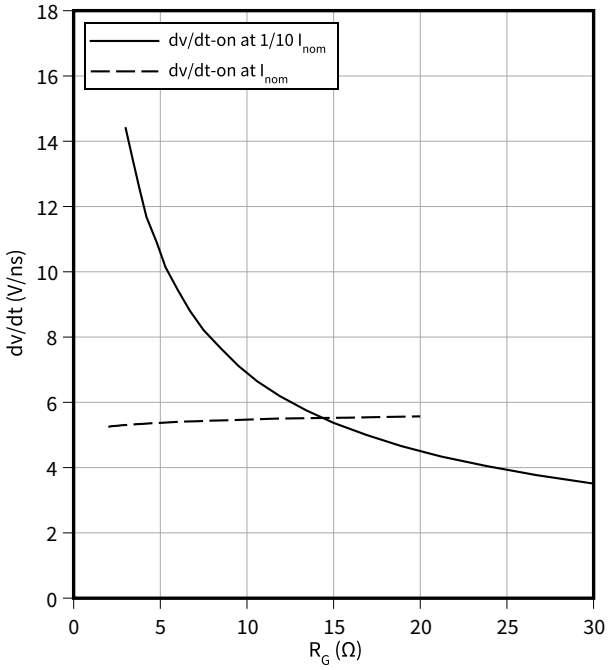
I_C = 35 A, V_{CC} = 600 V, -15 / 15 V, T_{vj} = 150 °C



Voltage slope (typical), IGBT, T1-T6

$dv/dt = f(R_G)$

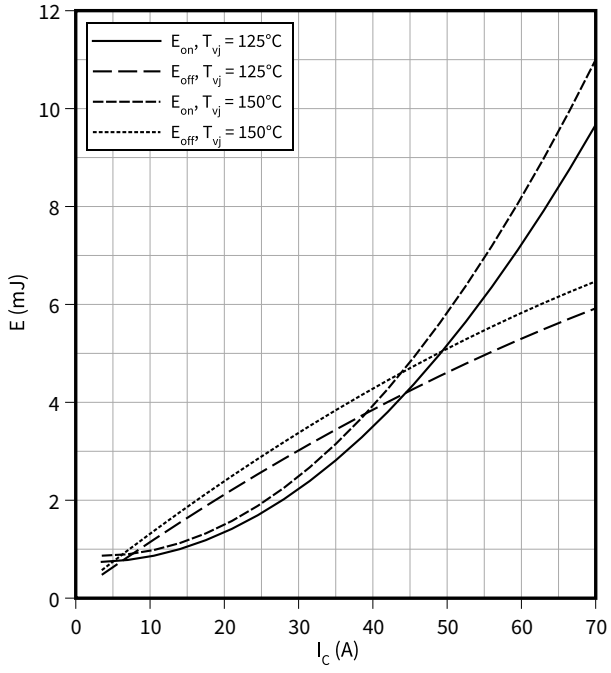
I_C = 35 A, V_{CE} = V, ±15 V, T_{vj} = 25 °C



Switching losses (typical), IGBT, T1-T6

$E = f(I_C)$

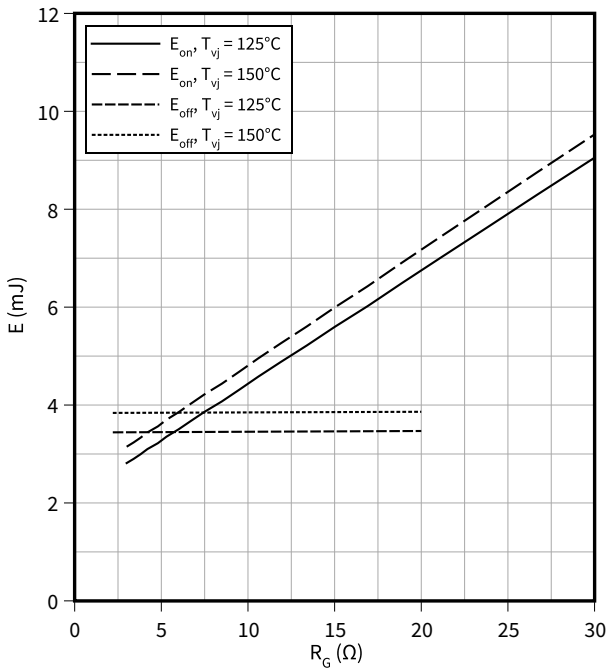
R_{Goff} = 2 Ω, R_{Gon} = 3 Ω, V_{CC} = 600 V, -15 / 15 V



Switching losses (typical), IGBT, T1-T6

$E = f(R_G)$

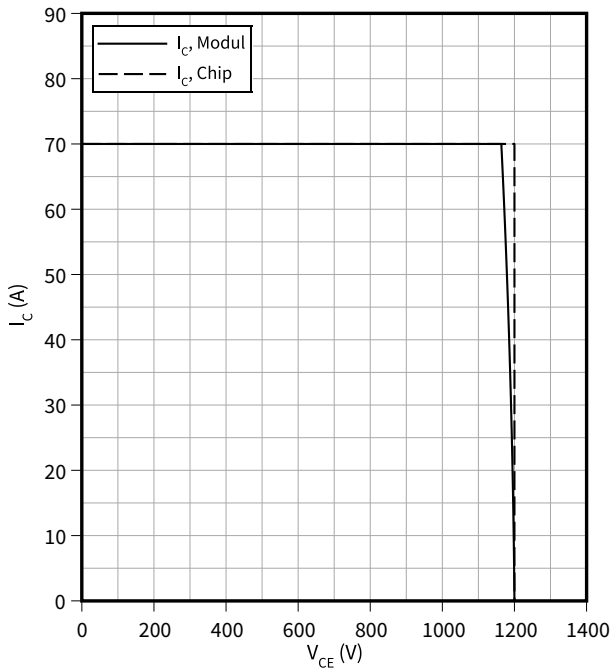
I_C = 35 A, V_{CC} = 600 V, -15 / 15 V



Reverse bias safe operating area (RBSOA), IGBT, T1-T6

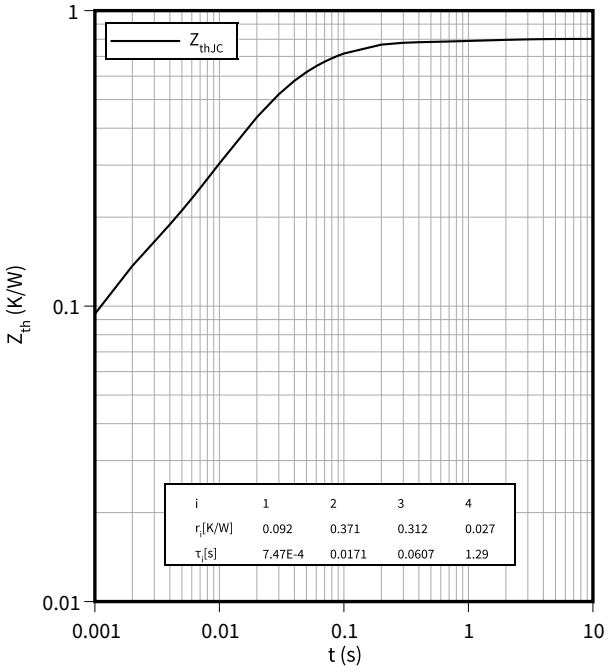
$I_C = f(V_{CE})$

T_{vj} = 150 °C, R_{Goff} = 2 Ω, V_{GE} = ±15 V



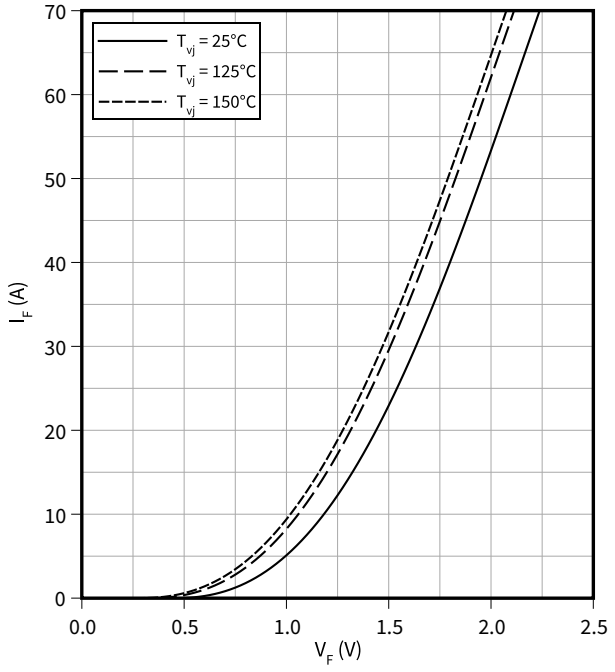
Transient thermal impedance, IGBT, T1-T6

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, D1-D6

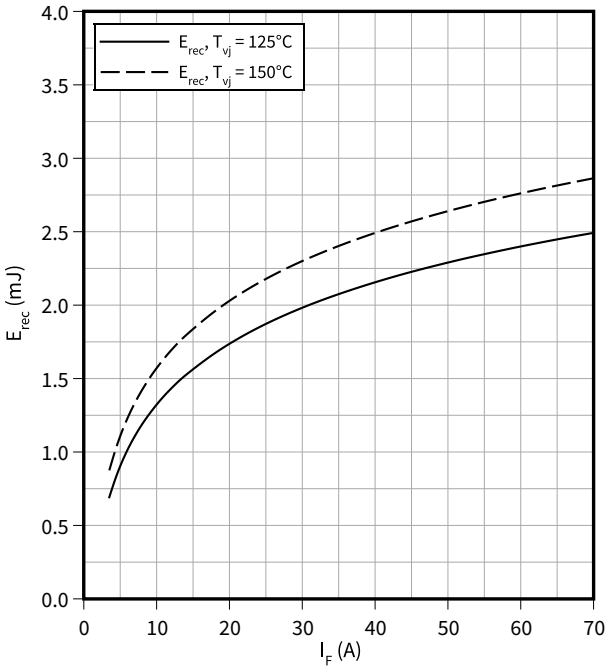
$I_F = f(V_F)$



Switching losses (typical), Diode, D1-D6

$E_{rec} = f(I_F)$

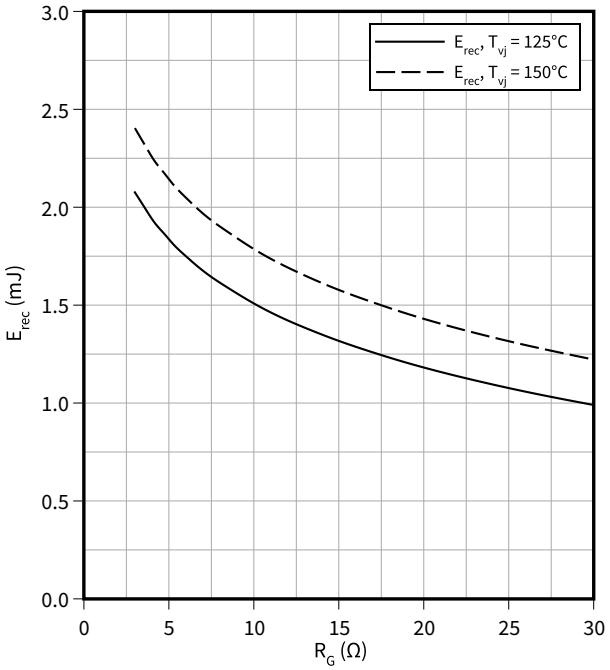
$R_{Gon} = 3\ \Omega$, $V_{CE} = 600$ V



Switching losses (typical), Diode, D1-D6

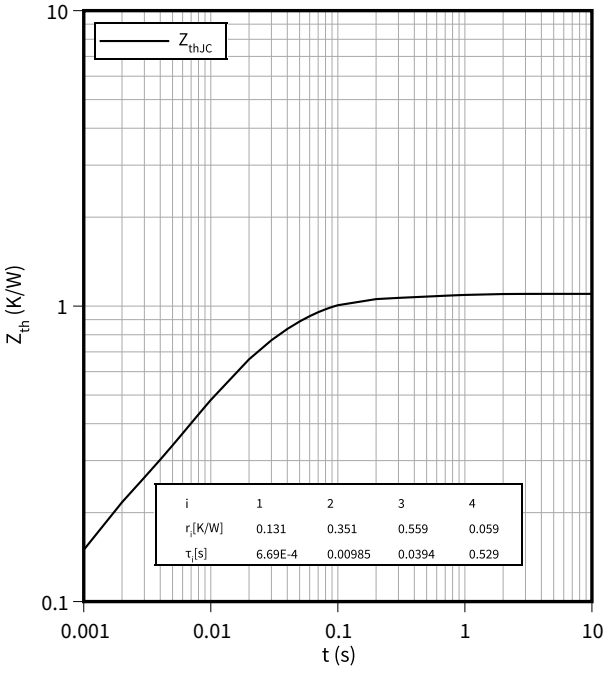
$E_{rec} = f(R_G)$

$V_{CE} = 600$ V, $I_F = 35$ A



Transient thermal impedance, Diode, D1-D6

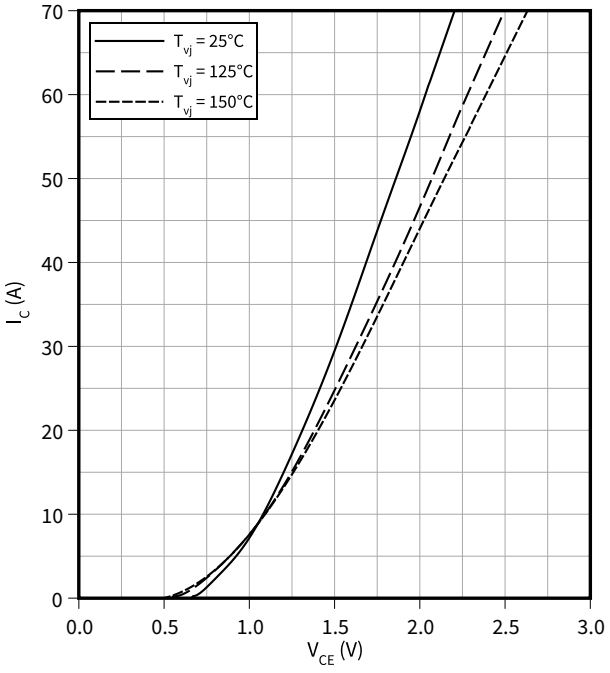
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, T7-T12

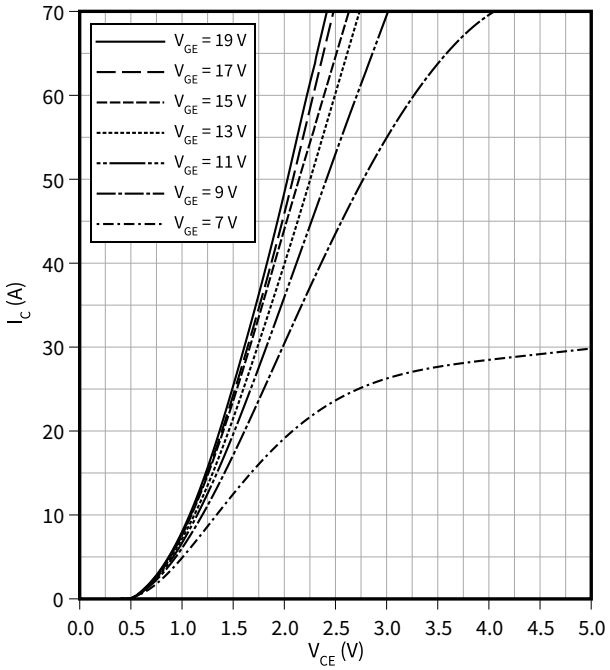
$I_C = f(V_{CE})$

$V_{GE} = 15$ V



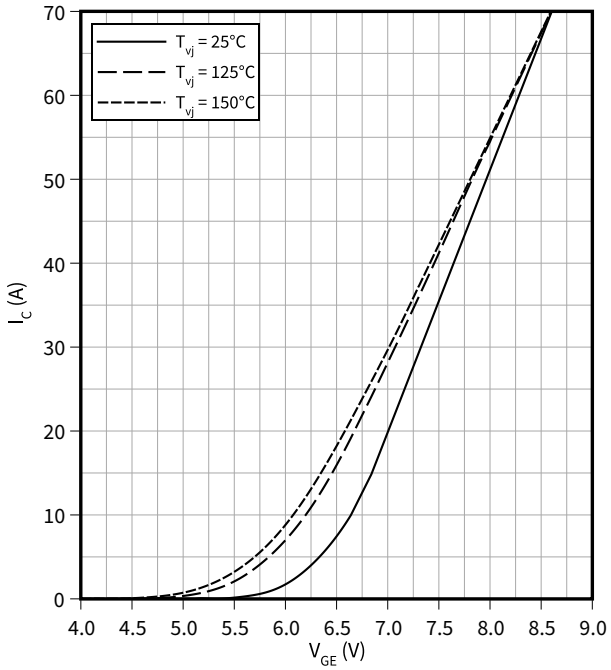
Output characteristic field (typical), IGBT, T7-T12

$I_C = f(V_{CE})$
$T_{vj} = 150\ °C$



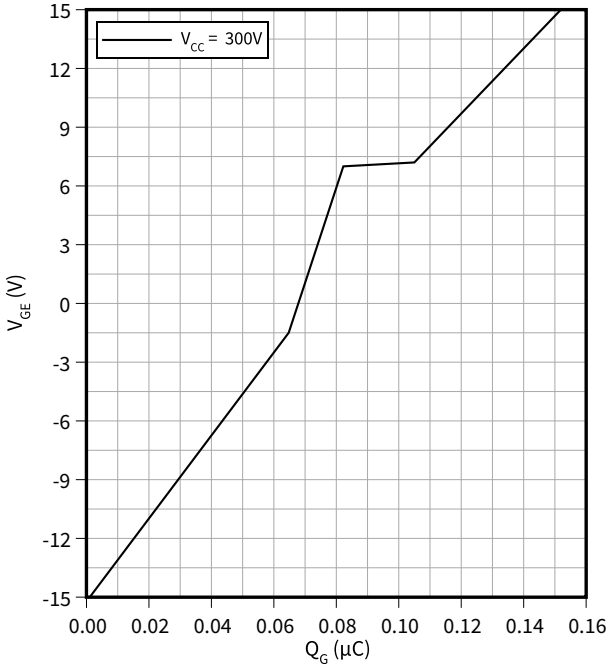
Transfer characteristic (typical), IGBT, T7-T12

$I_C = f(V_{GE})$
$V_{CE} = 20\ V$



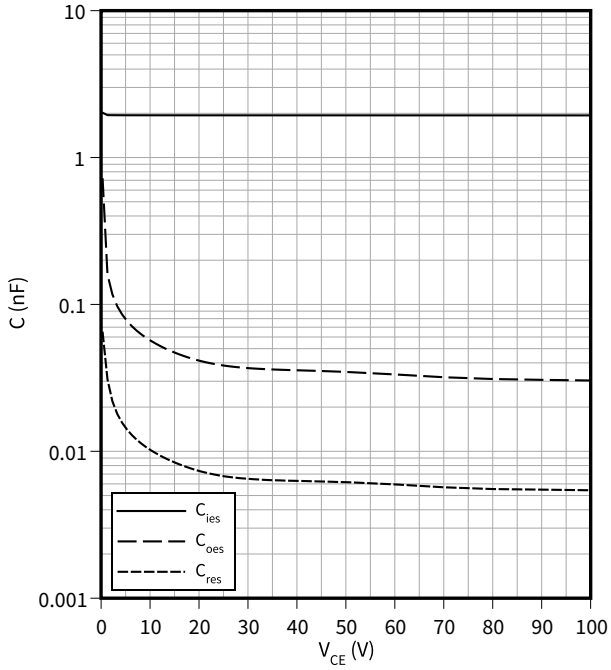
Gate charge characteristic (typical), IGBT, T7-T12

$V_{GE} = f(Q_G)$
$I_C = 35\ A,\ T_{vj} = 25\ °C$



Capacity characteristic (typical), IGBT, T7-T12

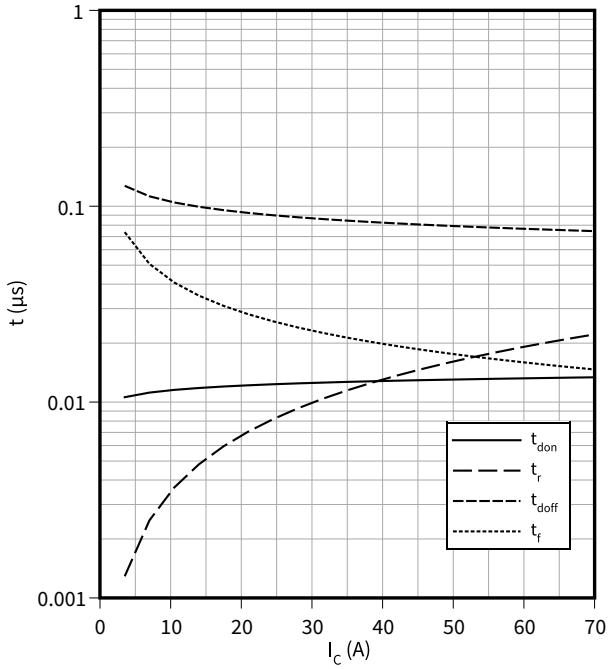
$C = f(V_{CE})$
$f = 100\ kHz,\ V_{GE} = 0\ V,\ T_{vj} = 25\ °C$



Switching times (typical), IGBT, T7-T12

$t = f(I_C)$

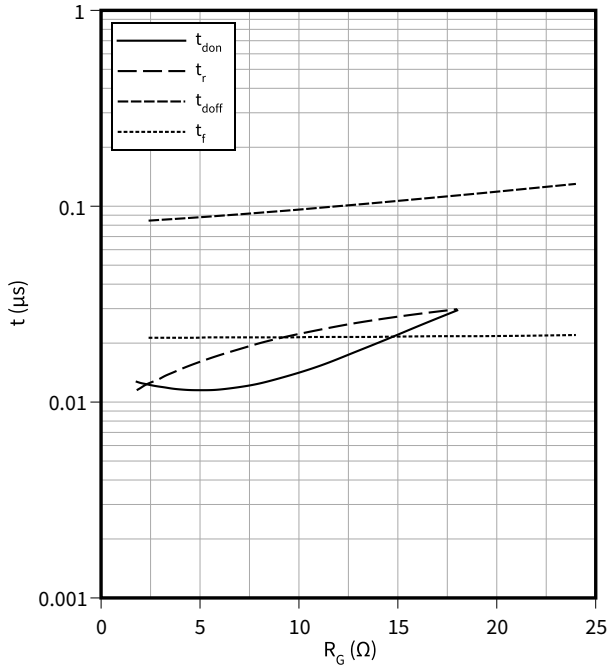
R_{Goff} = 2.4 Ω, R_{Gon} = 1.8 Ω, V_{CC} = 300 V, -15 / 15 V, T_{vj} = 150 °C



Switching times (typical), IGBT, T7-T12

$t = f(R_G)$

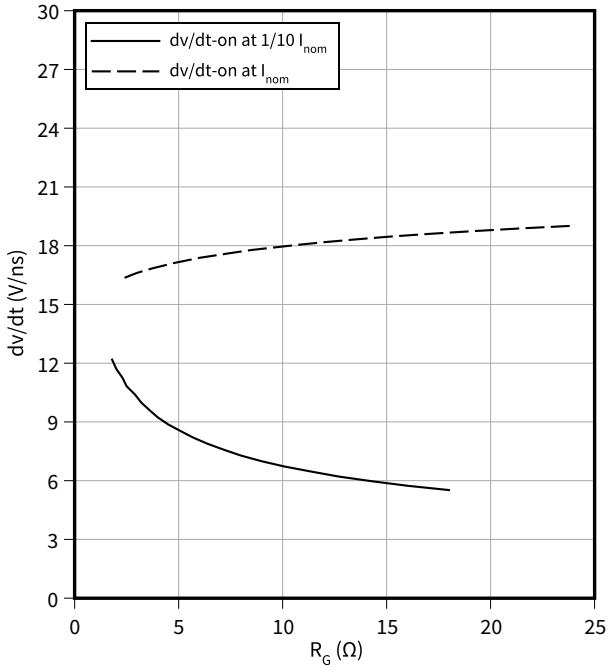
I_C = 35 A, V_{CC} = 300 V, -15 / 15 V, T_{vj} = 150 °C



Voltage slope (typical), IGBT, T7-T12

$dv/dt = f(R_G)$

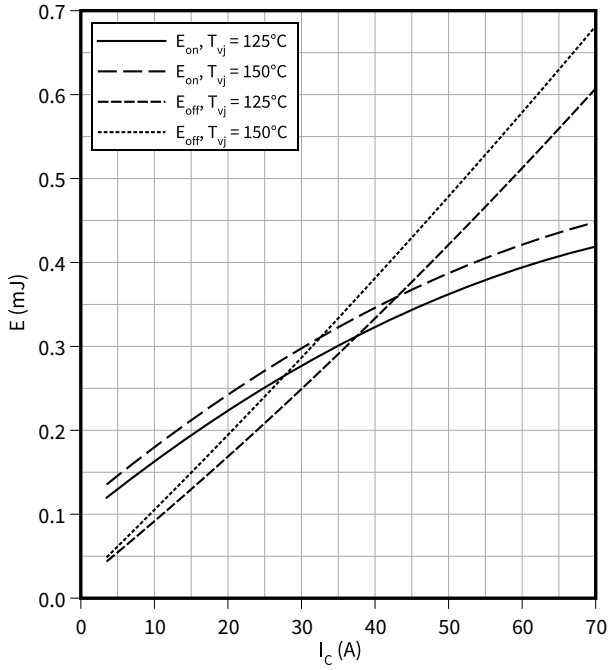
I_C = 35 A, V_{CE} = V, ±15 V, T_{vj} = 25 °C



Switching losses (typical), IGBT, T7-T12

$E = f(I_C)$

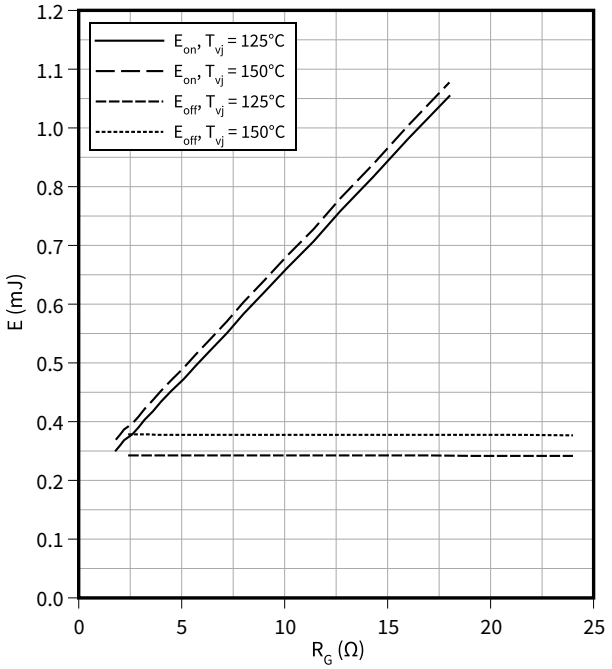
R_{Goff} = 2.4 Ω, R_{Gon} = 1.8 Ω, V_{CC} = 300 V, -15 / 15 V



Switching losses (typical), IGBT, T7-T12

$E = f(R_G)$

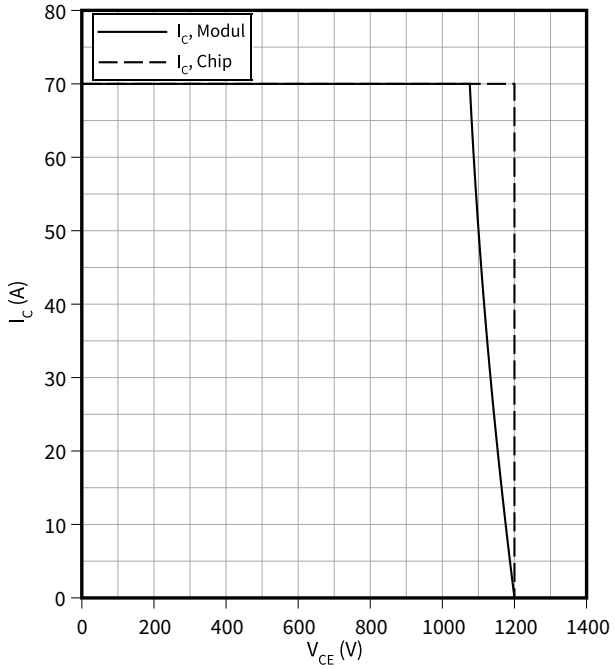
$I_C = 35\ A$, $V_{CC} = 300\ V$, -15 / 15 V



Reverse bias safe operating area (RBSOA), IGBT, T7-T12

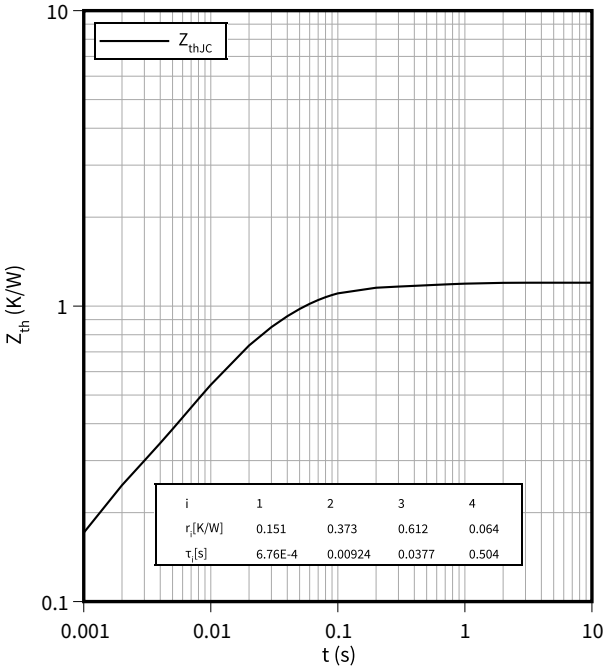
$I_C = f(V_{CE})$

$R_{Goff} = 2.4\ \Omega$, $V_{GE} = \pm 15\ V$, $T_{vj} = 150\ °C$



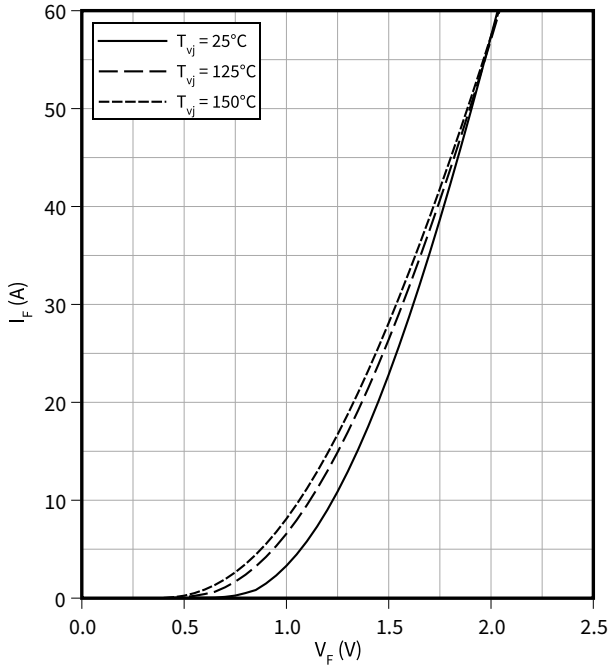
Transient thermal impedance, IGBT, T7-T12

$Z_{th} = f(t)$



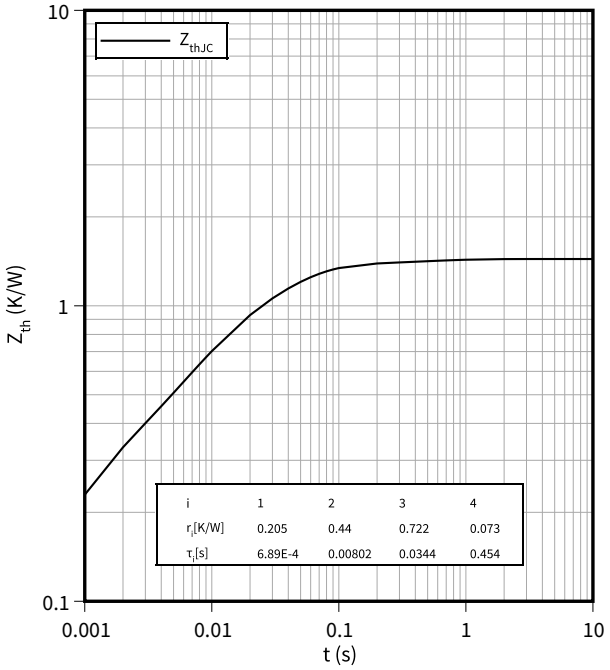
Forward characteristic (typical), Diode, D7-D12

$I_F = f(V_F)$



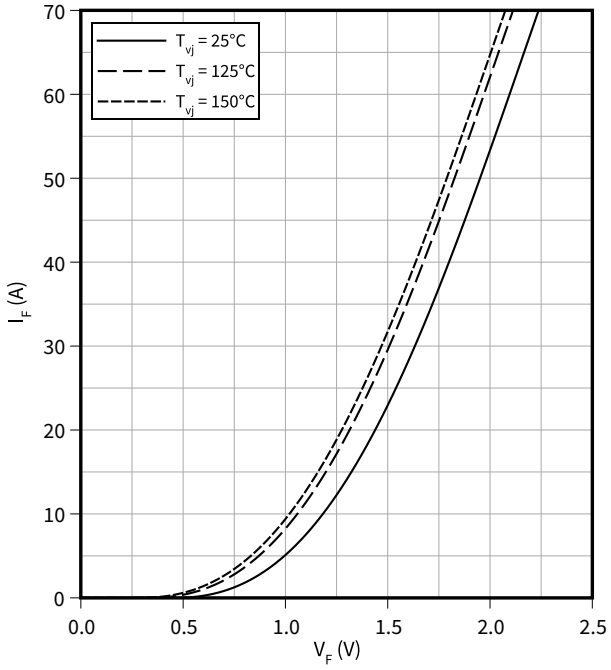
Transient thermal impedance, Diode, D7-D12

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, D13-D18

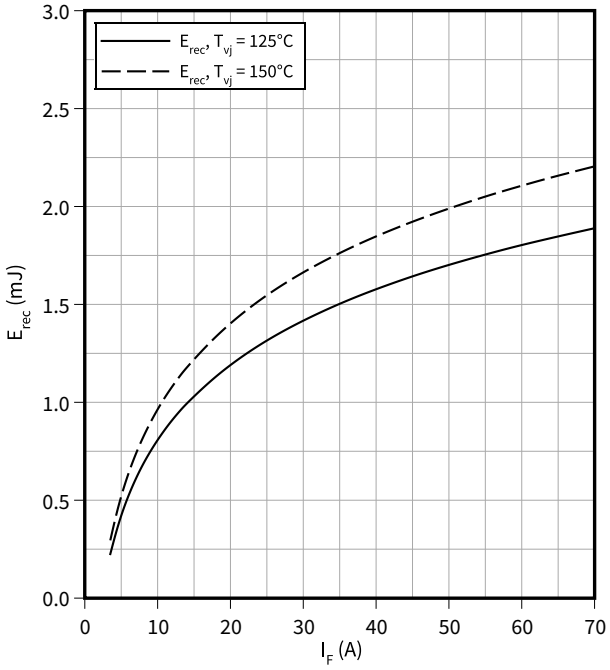
$I_F = f(V_F)$



Switching losses (typical), Diode, D13-D18

$E_{rec} = f(I_F)$

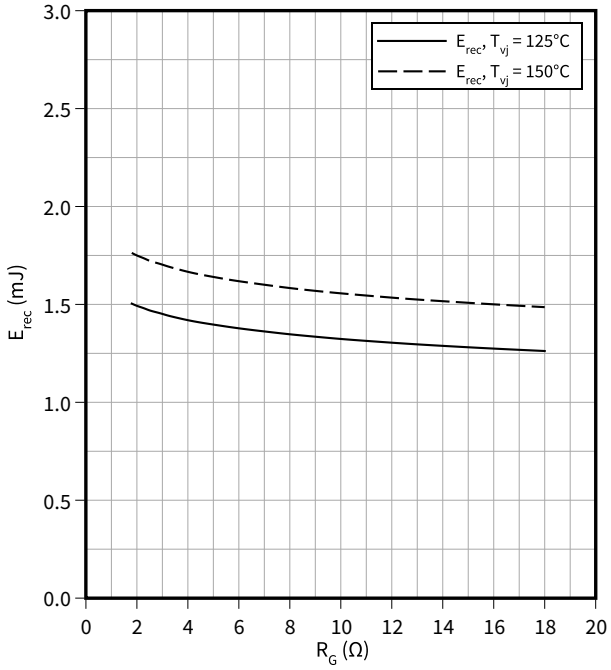
$R_{Gon} = 2.4\ \Omega$, $V_{CE} = 300\ V$



Switching losses (typical), Diode, D13-D18

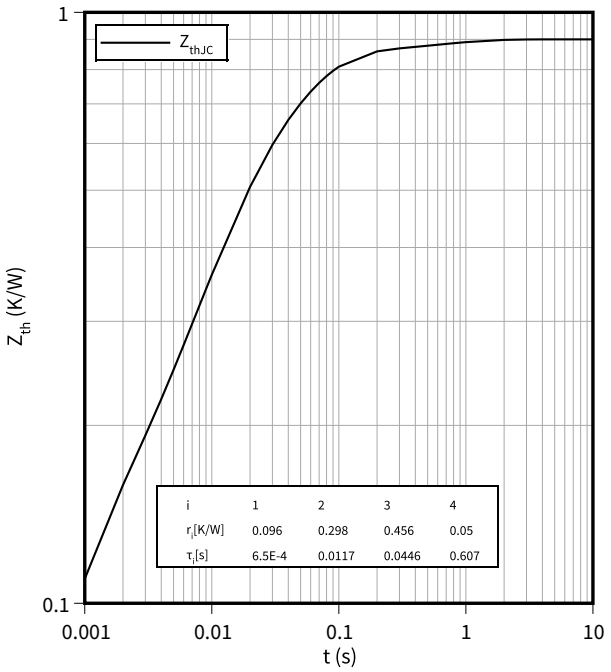
$E_{rec} = f(R_G)$

$V_{CE} = 300\ V$, $I_F = 35\ A$



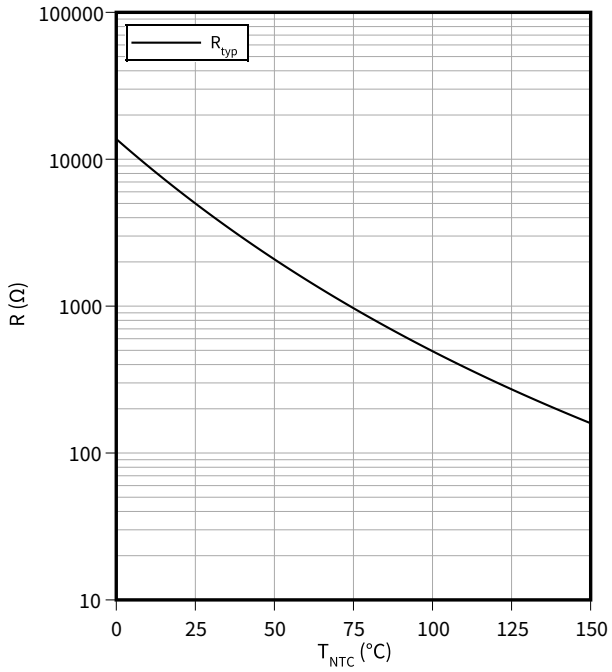
Transient thermal impedance, Diode, D13-D18

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

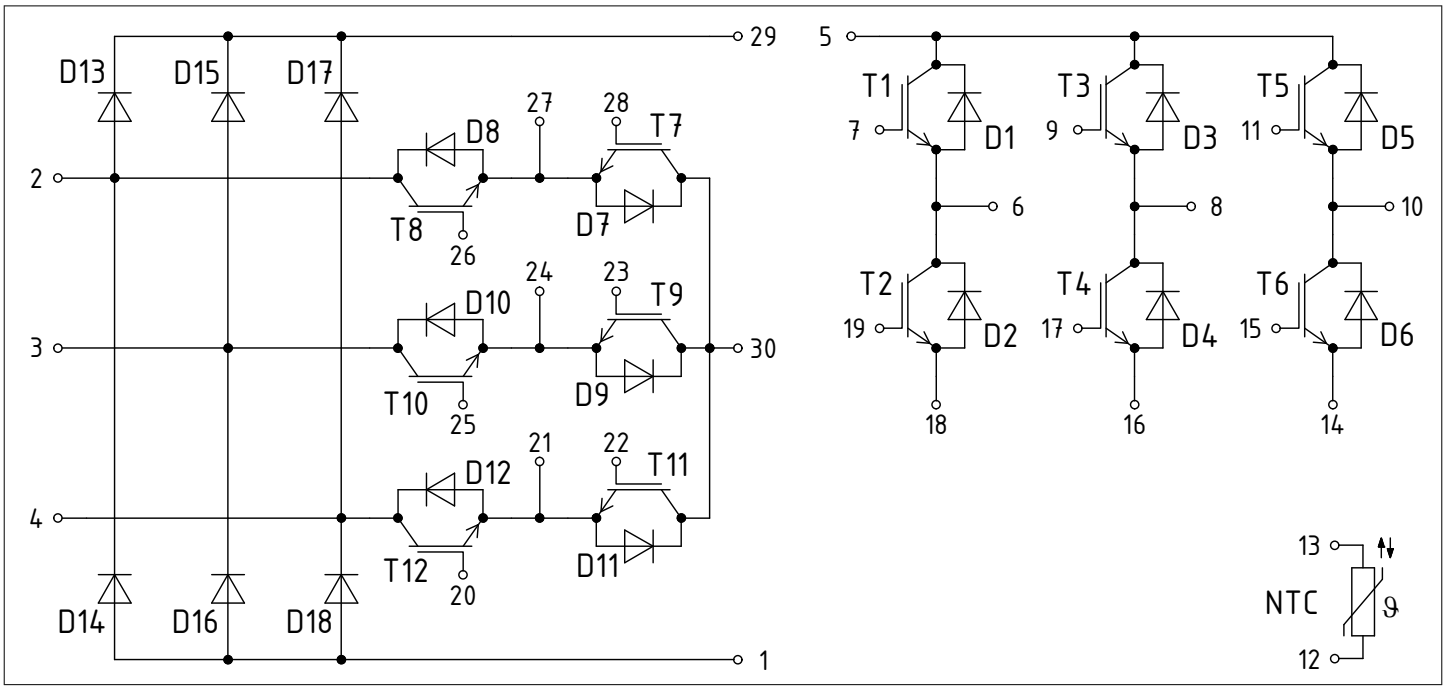


Figure 1

10 Package outlines

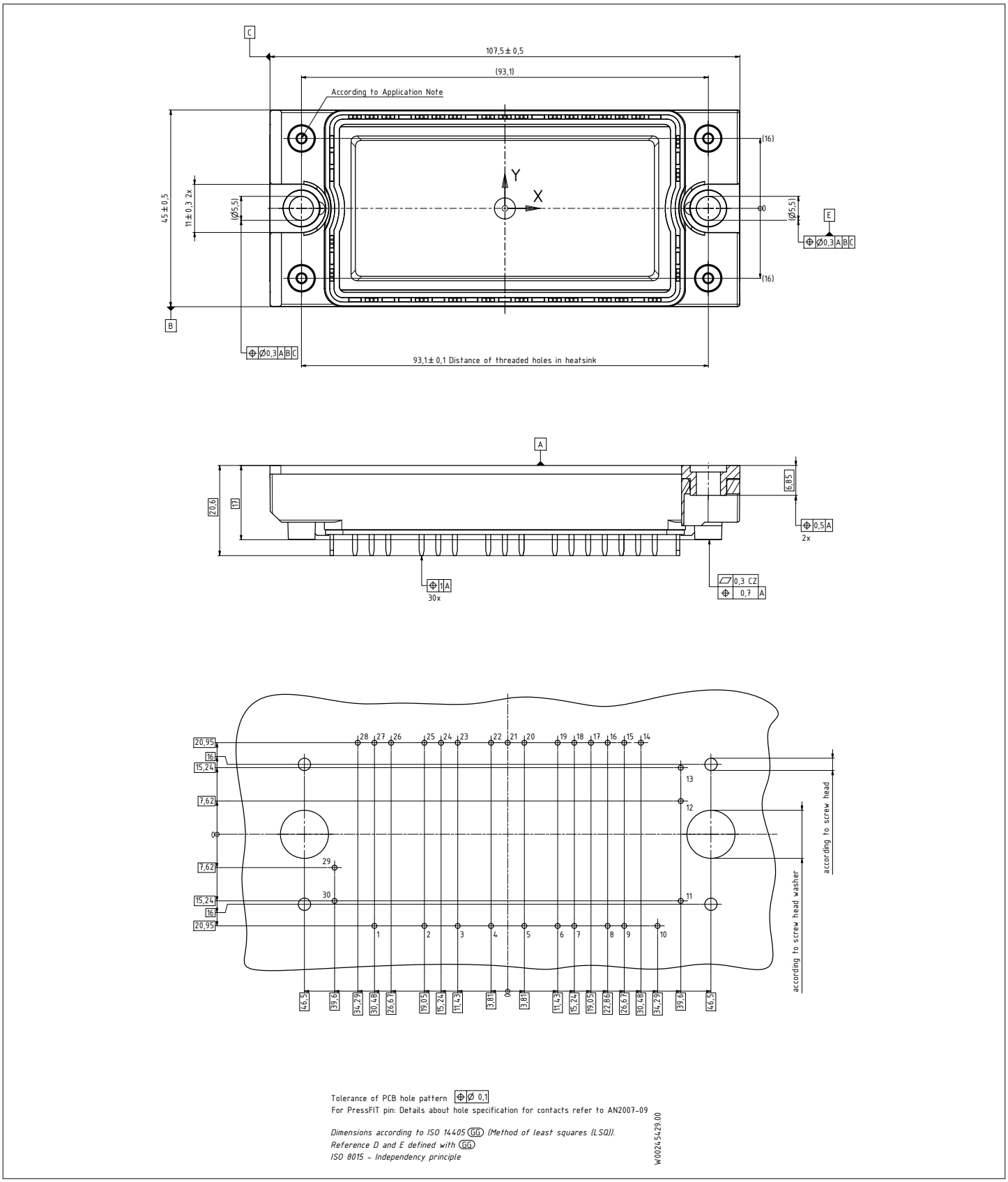


Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	7154914284655054991530		7154914284655054991530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2024-03-04	Initial version
0.20	2024-09-04	Preliminary datasheet

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